

In the Claims

The following Listing of Claims replaces all prior versions in the application:

LISTING OF CLAIMS

1. (Currently amended) Self aligned MIS transistor (1)-having a source zone (16,30,34) and a drain zone (18,32,36) on either side of a channel zone (20), said source and drain zones comprising a buried zone in a structure and a raised zone stacked on the buried zone, as well as a T shaped gate structure comprising:

a vertical bar (6) located above the channel zone (20), surmounted by a horizontal bar (8) extending on either side of the vertical bar (6), said horizontal bar (8) having a lower part (81), a lateral part (82) and an upper part (83), the gate structure consisting of a stacking of one or several conductive layers (69), a base zone of the gate structure being defined as being around the base of the vertical bar (6) of the T,

wherein transistor in which the gate structure is coated with a shaping material (14), said shaping material covering the vertical bar (6) of the T, and the lower (81) and lateral (82) parts of the horizontal bar (8) of the T, and the base zone of the T, said base zone of the gate structure covered by the shaping material covering at least a part of the buried zone (16,18) of the source and drain zone and not the raised zone of the source and drain zones

~~characterized in that said shaping material (14) also covers the base zone of the T shaped structure.~~

2. (Canceled)

3. (Currently amended) Self aligned MIS transistor (1) according to claim 1, further comprising characterised in that the first extension zones (42,44) located between the channel (20) and source and drain (16,18) zones respectively ~~have~~ and having a doping of the same nature as the sources and drain zones (16,18) but weaker.

4. (Currently amended) Self aligned MIS transistor (1) according to claim 1, further comprising characterised in that the second extension zones (45,46) located between the channel (20) and source and drain (16,18) zones respectively ~~have~~ and having a doping of nature opposite to that of the source and drain zones.

5. (Currently amended) Self aligned MIS transistor (1) according to claim 3, characterised in that the second extension zones (45,46) between the first extension zones (42,44) and the channel zone (20) have respectively a doping of nature opposite to that of the source and drain zones (16,18).

6. (Currently amended) Self aligned MIS transistor (1) according to claim 1, characterised in that the shaping material is of silicon nitride (Si_3N_4) or hafnium oxide (HfO_2) or zirconium oxide (ZrO_2) or aluminum oxide (Al_2O_3).

7. (Currently amended) Self aligned MIS transistor (1) according to claim 1, characterised in that the stacking of layers constituting the gate structure lodged in the shaping material (14) is intrinsic polysilicon or metal.

8. (Currently amended) Method for manufacturing, on a semiconductor substrate (2), at least one self aligned MIS transistor (1) having a source zone (16,30,34) and a drain zone (18,32,36) on either side of a channel zone (20), said source and drain zones comprising a buried zone in the substrate and a raised zone stacked on the buried zone, as well as a T shaped gate structure of low resistivity comprising a vertical bar (6) located above the channel zone (20), surmounted by a horizontal bar (8) extending on either side of the vertical bar (6), said horizontal bar (8) having a lower part (81), a lateral part (82) and an upper part (83), the gate structure ~~consisting of~~ comprising a stacking of one or several conductive layers (69), a base zone of the gate structure being defined as being around the base of the vertical bar (6) of the T, the method comprising a step of forming a solid shape having the T shape of the grid that one wishes to form, and the coating of said shape in a shaping material (14), said shaping material (14) coating the lateral surface (62) of the vertical bar (6) of the T, the lower (81) and lateral (82) surfaces of the horizontal bar of the T,

characterized in that wherein said shaping material (14) also covers the base zone of the definitive gate structure and at least a part of the buried zone of the source and drain zones and not of the raised zone of the source and drain zones.

9. (Canceled)

10. (Original) Method according to claim 8 characterised in that the shaping material is silicon nitride (Si_3N_4) or hafnium oxide (HfO_2) or zirconium oxide (ZrO_2) or aluminum oxide (Al_2O_3).